



N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)			
100	0.105 at V _{GS} = 10 V	4.2			
100	0.115 at V _{GS} = 4.5 V	3.9			

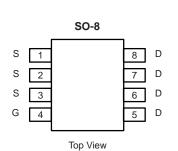
FEATURES

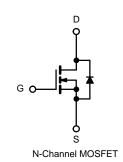
- TrenchFET® Power MOSFETS
- 175 °C Junction Temperature
- 100 % R_g Tested



APPLICATIONS

- Load Switch
- LED Backlighting in LCD TVs





ABSOLUTE MAXIMUM RATINGS (T_C =	= 25 °C, unless othe	rwise noted)			
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V _{DS}	100	V		
Gate-Source Voltage	V _{GS}	± 20]		
Continuous Drain Current (T _{.I} = 175 °C) ^b	T _C = 25 °C	1-	4.2		
Continuous Diain Current (1) = 175 C)	T _C = 125 °C	· I _D	3.2		
Pulsed Drain Current	I _{DM}	12.6	Α		
Continuous Source Current (Diode Conduction)	I _S	4.5			
Avalanche Current	I _{AR}	4.5			
Repetitive Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E _{AR}	1.8	mJ	
Maximum Power Dissipation	T _C = 25 °C	P _D	4.8 ^b	W	
iviaximum i ower bissipation	T _A = 25 °C	' D	2.4 ^a	V V	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 175	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
lunation to Ambiant	t ≤ 10 s	R _{thJA}	40	51	°C/W	
Junction-to-Ambient ^a	Steady State		18	25		
Junction-to-Case		R _{thJC}	2	2.4		

Notes:

- a. Surface mounted on 1" x 1" FR4 board.
- b. See SOA curve for voltage derating.



Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Static					l l		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	100			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1		3	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V _{DS} = 80 V, V _{GS} = 0 V			1		
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 \text{ °C}$			50	μA	
		V _{DS} = 80 V, V _{GS} = 0 V, T _J = 175 °C			250	1	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V			12.6	Α	
		V _{GS} = 10 V, I _D = 2.7 A		0.105	0.117		
D : 0	D	V _{GS} = 10 V, I _D = 2.5 A, T _J = 125 °C			0.129		
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 2.5 A, T _J = 175 °C			0.134	Ω	
		V _{GS} = 4.5 V, I _D = 2.5 A		0.115	0.128		
Forward Transconductance ^b	9 _{fs}	V _{DS} = 15 V, I _D = 2.5 A		7		S	
Dynamic ^a							
Input Capacitance	C _{iss}			1561			
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 80 \text{ V}, f = 1 \text{ MHz}$		110		pF	
Reverse Transfer Capacitance	C _{rss}			65			
Total Gate Charge ^c	Q_g			7	11		
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 80 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 15 \text{ A}$		2.1		nC	
Gate-Drain Charge ^c	Q_{gd}			2.6			
Gate Resistance	R _g			3		Ω	
Turn-On Delay Time ^c	t _{d(on)}			10			
Rise Time ^c	t _r	$V_{DD} = 80 \text{ V}, R_L = 5 \Omega$		16			
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 15 \text{ A}, V_{GEN} = 10 \text{ V}, R_G = 2.5 \Omega$		11		ns	
Fall Time ^c	t _f			15			
Source-Drain Diode Ratings and Cha	racteristic (T	_C = 25 °C)					
Pulsed Current	I _{SM}				12.6	Α	
Diode Forward Voltage ^b	V_{SD}	$I_F = 15 \text{ A}, V_{GS} = 0 \text{ V}$		0.8	1.2	V	
Source-Drain Reverse Recovery Time	t _{rr}	$I_F = 15 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}$		50	80	ns	

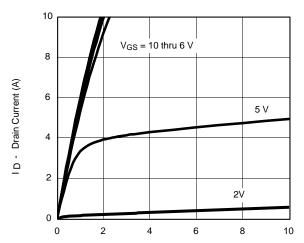
Notes:

- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

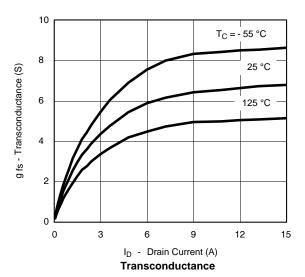


TYPICAL CHARACTERISTICS (25 °C unless noted)



V_{DS} - Drain-to-Source Voltage (V)





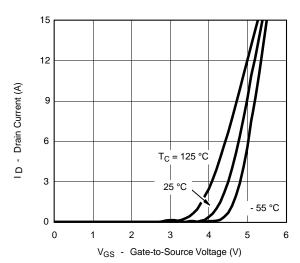
2000
1600
Ciss
1200
400
Crss
Coss

20

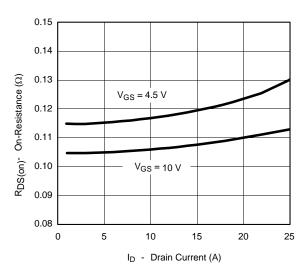
V_{DS} - Drain-to-Source Voltage (V) **Capacitance**

60

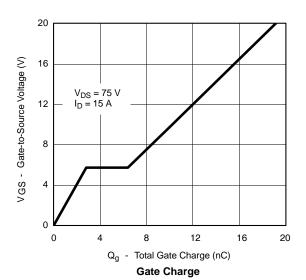
100



Transfer Characteristics

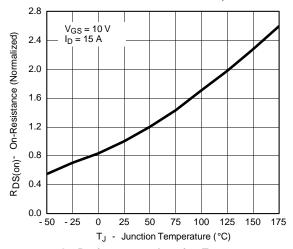


On-Resistance vs. Drain Current



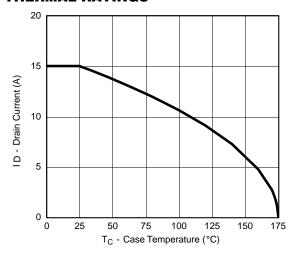


TYPICAL CHARACTERISTICS (25 °C unless noted)

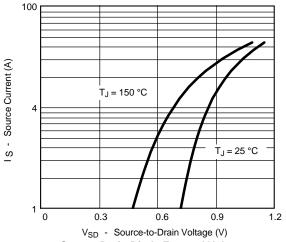


On-Resistance vs. Junction Temperature

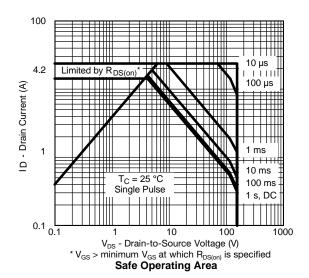
THERMAL RATINGS



Maximum Avalanche Drain Current vs. Case Temperature



Source-Drain Diode Forward Voltage

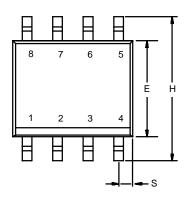


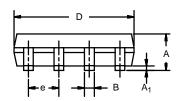
Normalized Thermal Transient Impedance, Junction-to-Case

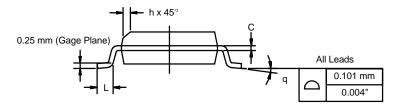




SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







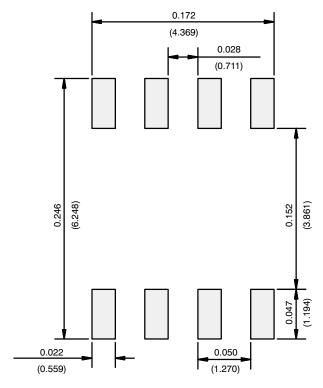
	MILLIM	IETERS	INCHES			
DIM	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A ₁	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
E	3.80	4.00	0.150	0.157		
е	1.27	1.27 BSC		0.050 BSC		
Н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-06527-Pey I 11-Sep-06						

ECN: C-06527-Rev. I, 11-Sep-06

DWG: 5498



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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